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LI(10) **Pub. No.: US 2023/0232615 A1**(43) **Pub. Date: Jul. 20, 2023**(54) **METHOD OF MANUFACTURING
SEMICONDUCTOR STRUCTURE AND
SEMICONDUCTOR STRUCTURE**(71) Applicant: **CHANGXIN MEMORY
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(CN)(72) Inventor: **Guangji LI**, Hefei City (CN)(21) Appl. No.: **17/804,937**(22) Filed: **Jun. 1, 2022****Related U.S. Application Data**(63) Continuation of application No. PCT/CN2022/
078996, filed on Mar. 3, 2022.(30) **Foreign Application Priority Data**

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(2013.01); **H01L 27/10805** (2013.01)(57) **ABSTRACT**

The present disclosure discloses a method of manufacturing a semiconductor structure and a semiconductor structure, and relates to the technical field of semiconductors. The method includes: providing a base, active regions arranged at intervals along a first direction being arranged in the base; forming, on the base, bit line structures arranged at intervals; forming a contact structure between two adjacent ones of the bit line structures; forming a barrier structure on the contact structure, the barrier structures being arranged in correspondence with and connected to the bit line structure, and a first recess being formed between any adjacent barrier structures; and forming a conductive structure in the first recess, the conductive structure including a protective layer and a conductive portion, and the protective layer wrapping a sidewall and a bottom wall of the conductive portion.

